

About OMICS Group

OMICS Group International is an amalgamation of Open Access publications and worldwide international science conferences and events. Established in the year 2007 with the sole aim of making the information on Sciences and technology 'Open Access', OMICS Group publishes 400 online open access scholarly journals in all aspects of Science, Engineering, Management and Technology journals. OMICS Group has been instrumental in taking the knowledge on Science & technology to the doorsteps of ordinary men and women. Research Scholars, Students, Libraries, Educational Institutions, Research centers and the industry are main stakeholders that benefitted greatly from this knowledge dissemination. OMICS Group also organizes 300 International conferences annually across the globe, where knowledge transfer takes place through debates, round table discussions, poster presentations, workshops, symposia and exhibitions.

About OMICS Group Conferences

OMICS Group International is a pioneer and leading science event organizer which publishes around 400 open access journals and conducts over 300 Medical, Clinical, Engineering, Life Sciences, Pharma scientific conferences all over the globe annually with the support of more than 1000 scientific associations and 30,000 editorial board members and 3.5 million followers to its credit.

OMICS Group has organized 500 conferences, workshops and national symposiums across the major cities including San Francisco, Las Vegas, San Antonio, Omaha, Orlando, Raleigh, Santa Clara, Chicago, Philadelphia, Baltimore, United Kingdom, Valencia, Dubai, Beijing, Hyderabad, Bengaluru and Mumbai.

Interfaces between graphene and MoS₂ probed STM and ARPES

Matthias Batzill
University of South Florida, Tampa

At USF:

Horacio Coy-Diaz
Dr. Rafik Addou

Antares beamline at SOLEIL:

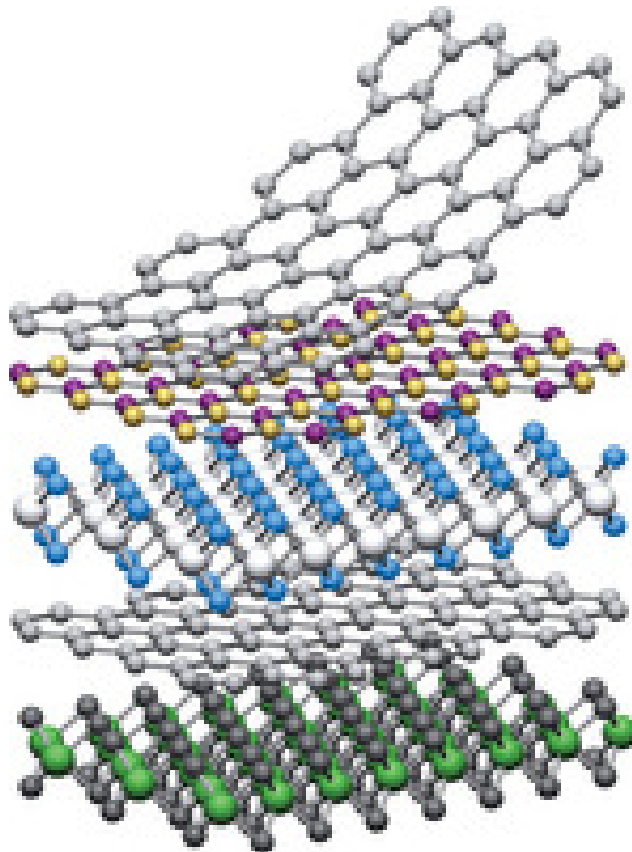
Dr. José Avila
Dr. Chaoyu Chen
Prof. Maria C. Asensio

Artificial crystals or device-structures made of 2D-materials

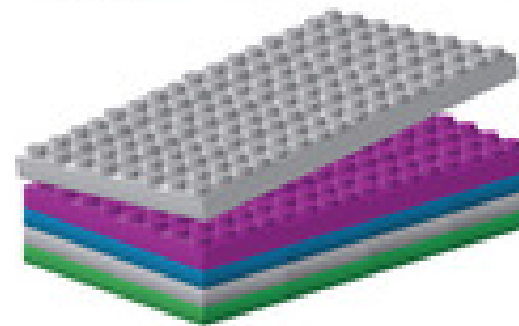
Van der Waals heterostructures

K. Geim^{1,2} & I. V. Grigorieva¹

25 JULY 2013 | VOL 499 | NATURE | 419



	Graphene	
	hBN	
	MoS ₂	
	WS ₂	
	Fluorographene	



How do interactions between layers modify properties?

05 (2010)

PHYSICAL REVIEW LETTERS

week ending
24 SEPTEMBER 2010

Atomically Thin MoS₂: A New Direct-Gap Semiconductor

Kin Fai Mak,¹ Changgu Lee,² James Hone,³ Jie Shan,⁴ and Tony F. Heinz^{1,*}

¹*Departments of Physics and Electrical Engineering, Columbia University, 538 West 120th Street, New York, New York 10027, USA*

²*SKKU Advanced Institute of Nanotechnology (SAINT) and Department of Mechanical Engineering, Sungkyunkwan University, Suwon 440-746, Korea*

³*Department of Mechanical Engineering, Columbia University, New York, New York 10027, USA*
⁴*Department of Physics, Case Western Reserve University, 10900 Euclid Avenue, Cleveland, Ohio 44106, USA*

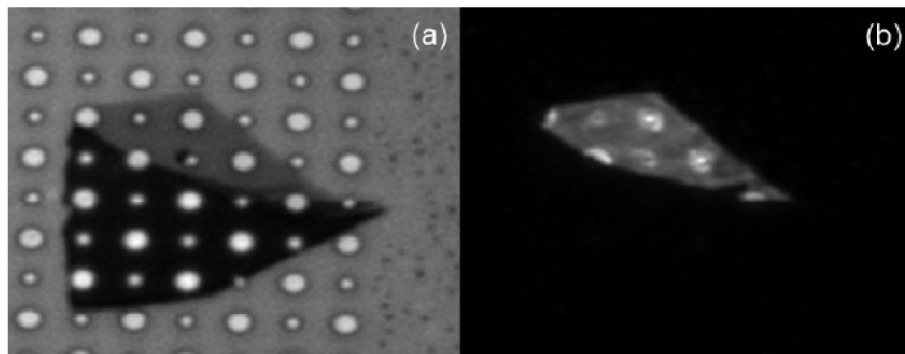
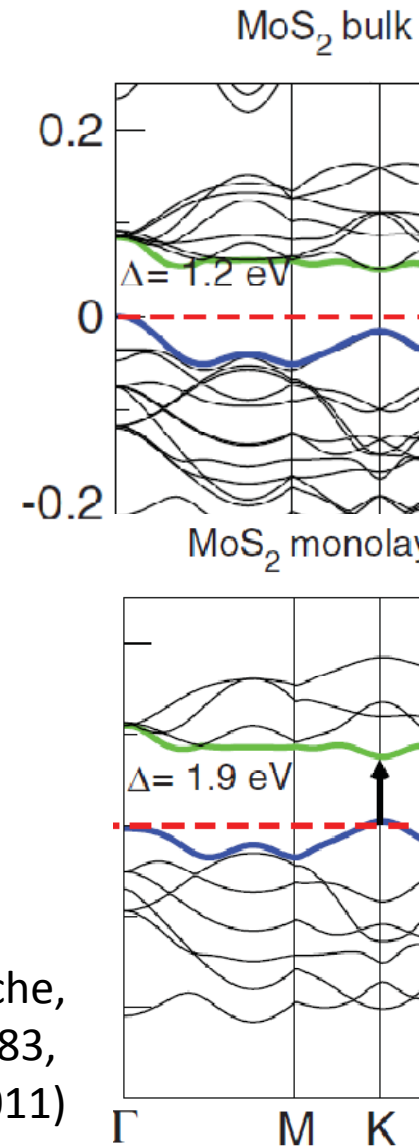


FIG. 2. (a) Representative optical image of mono- and few-layer MoS₂ crystals on a silicon substrate with etched holes of 1.0 and 1.5 μm in diameter. (b) PL image of the same samples. The PL QY is much enhanced for suspended regions of the monolayer samples, and the emission from the few-layer sample is too weak to be seen in this image.

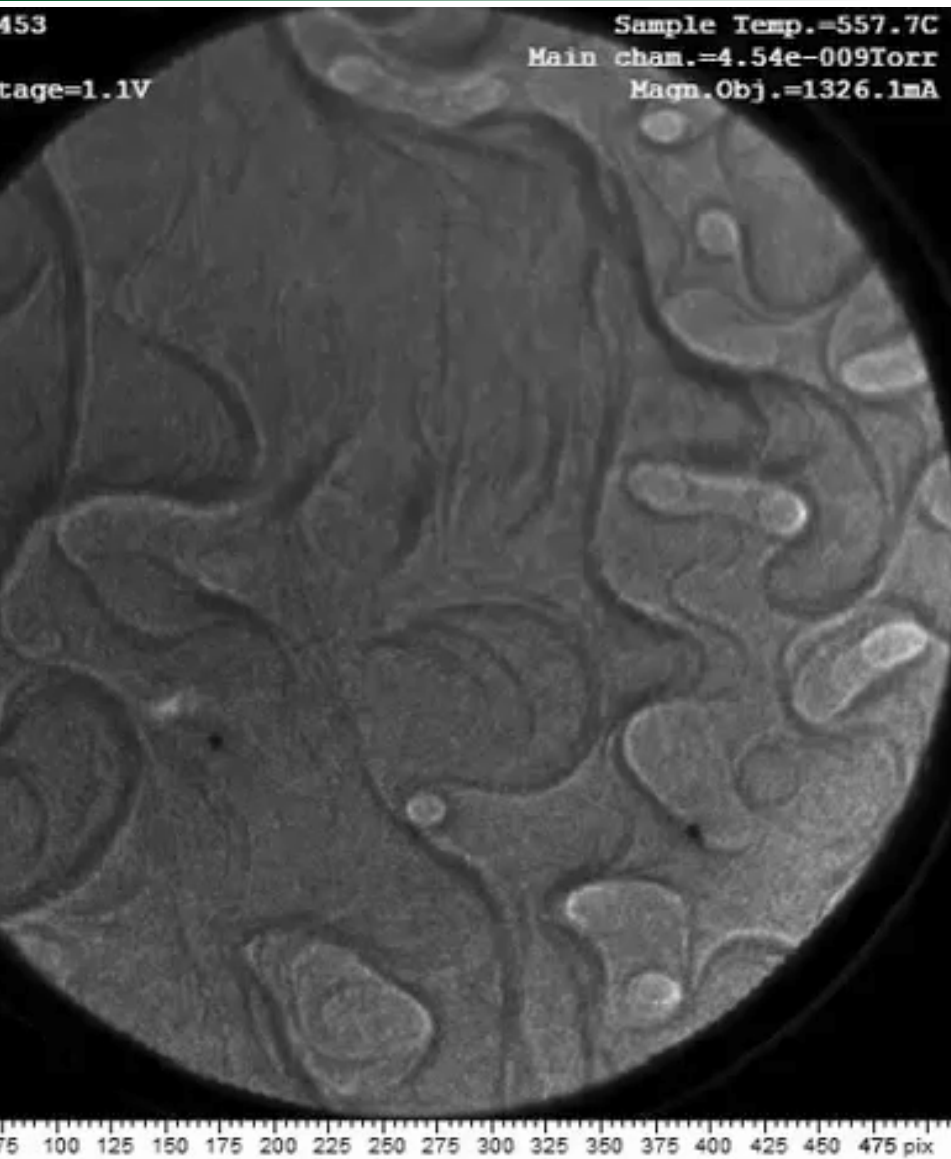


Kuc, Zibouche,
Heine PRB 83,
245213 (2011)

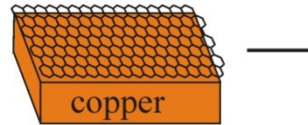
If interlayer interactions are important for the electronic structure of van der Waals materials, how do interlayer interactions affect heterostructures of van der Waals materials?

Here we study graphene/MoS₂ interfaces.

Preparation of graphene/MoS₂ samples

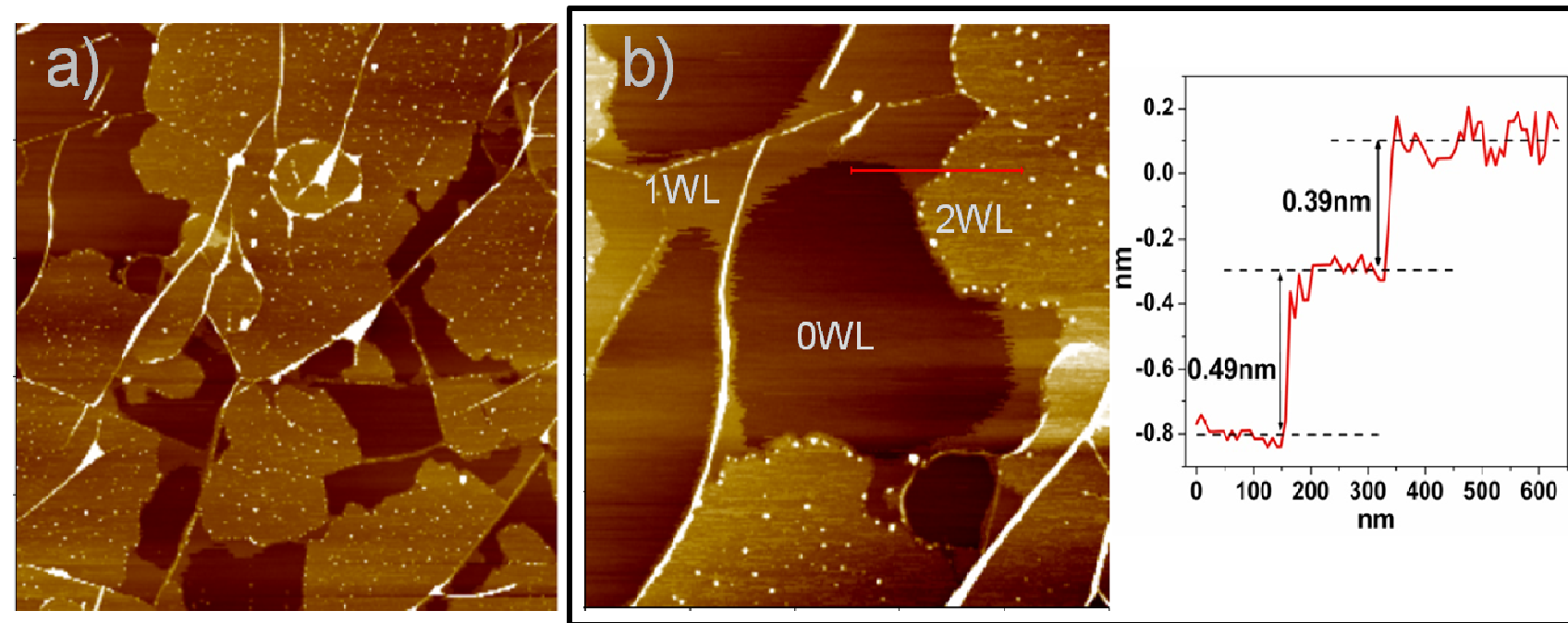


1. chemical vapor deposition (CVD) synthesis of graphene on metal



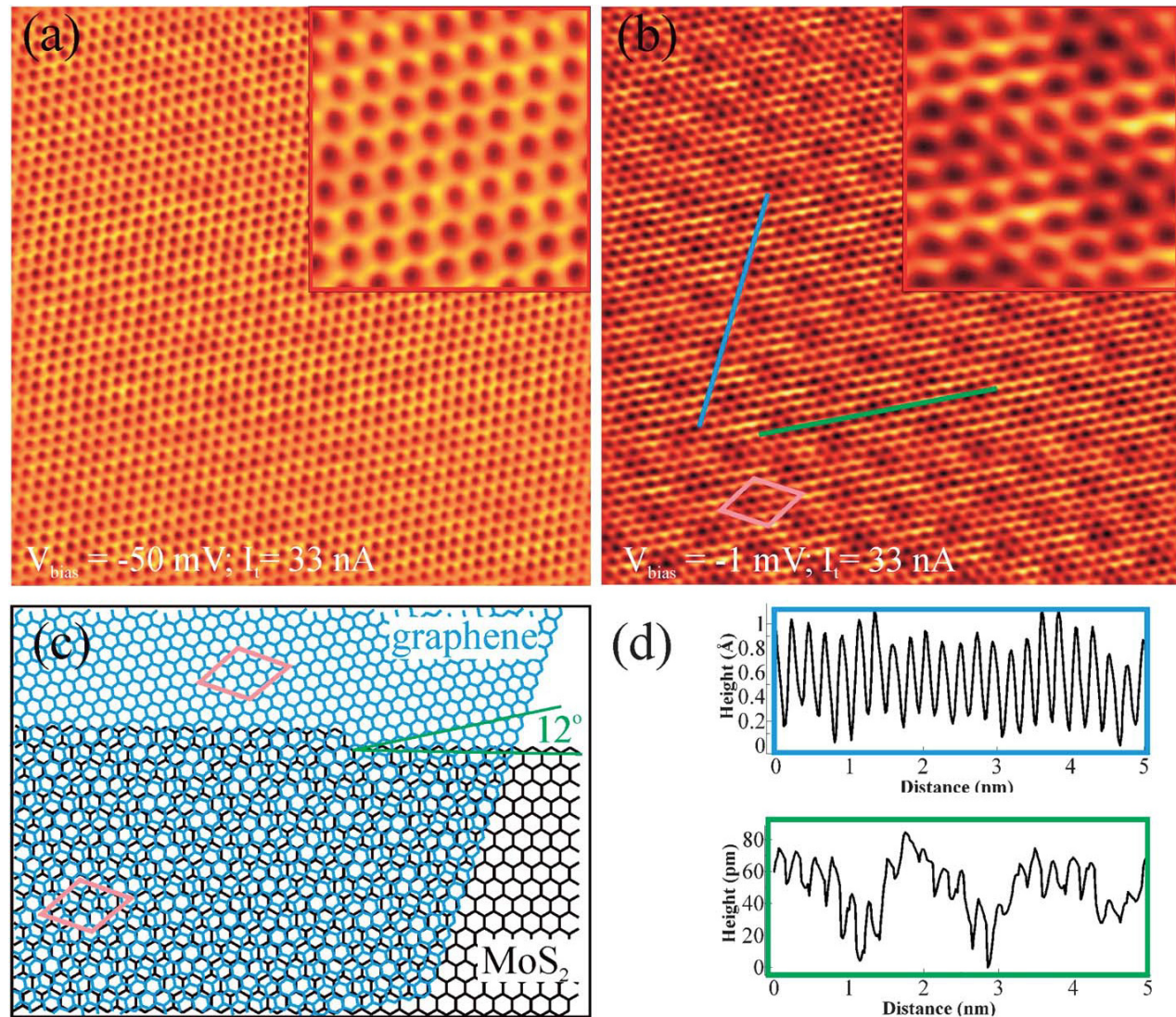
Characterization of transferred graphene on MoS₂

water-layer after transfer (ambient AFM)

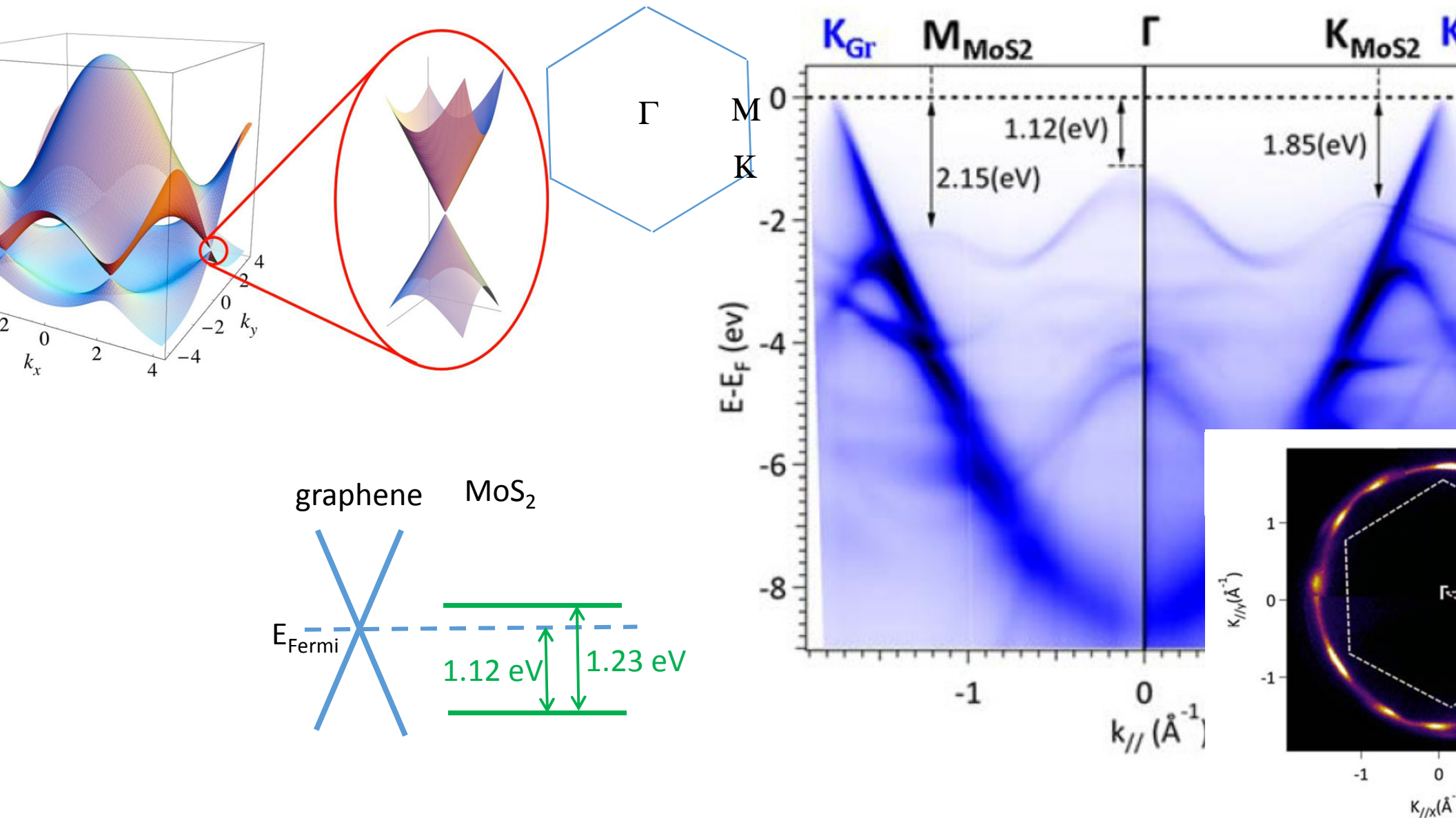


Characterization of transferred graphene on MoS₂

annealing in UHV at 300 C:
sharply sharp interface => moire

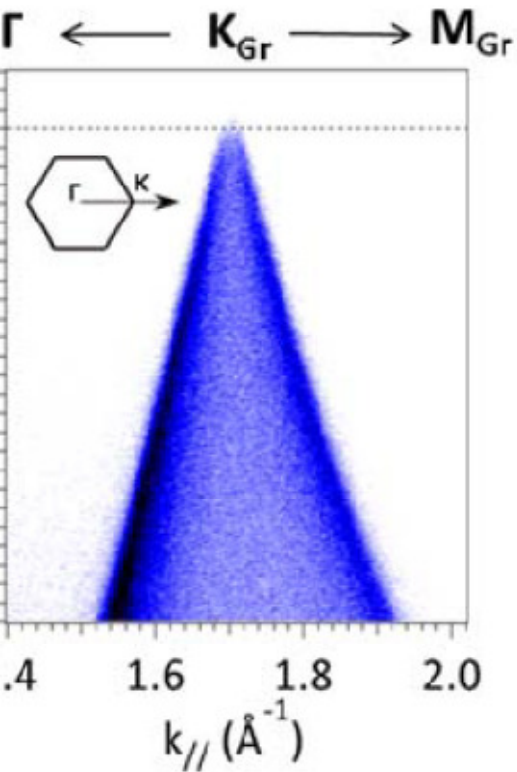


Electronic structure of transferred graphene on MoS₂

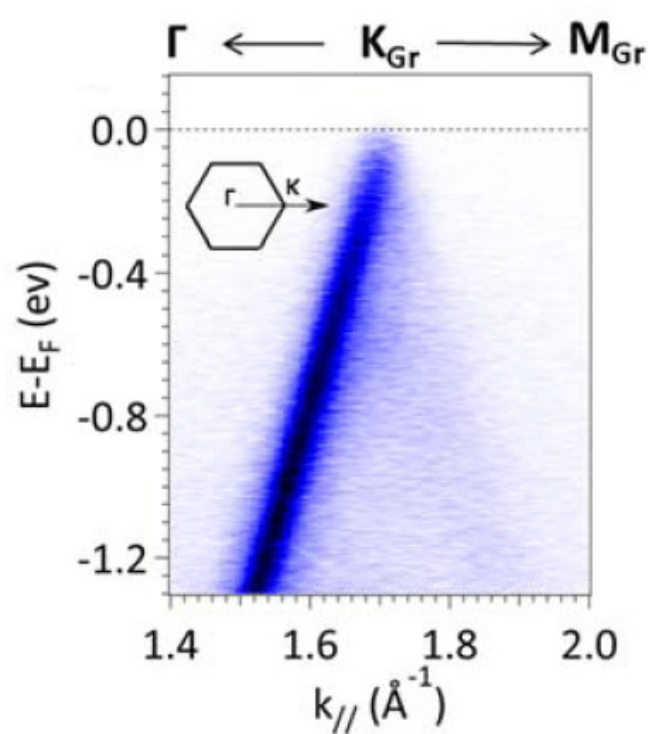


Intact Dirac-cone with no charge transfer doping

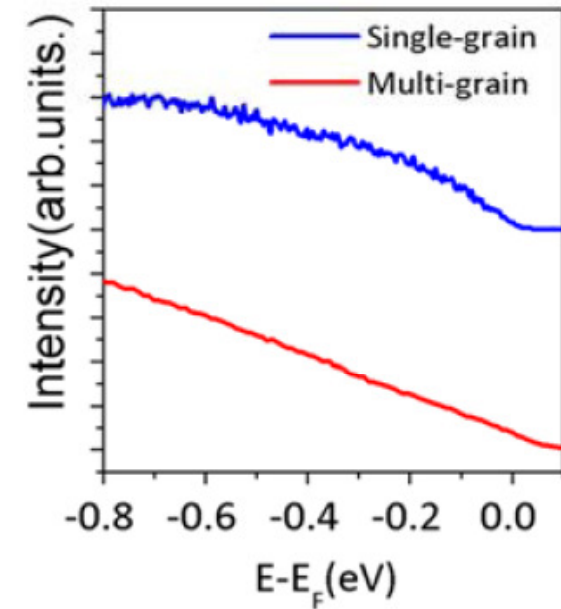
(30 eV)



NanoARPES (100 eV)



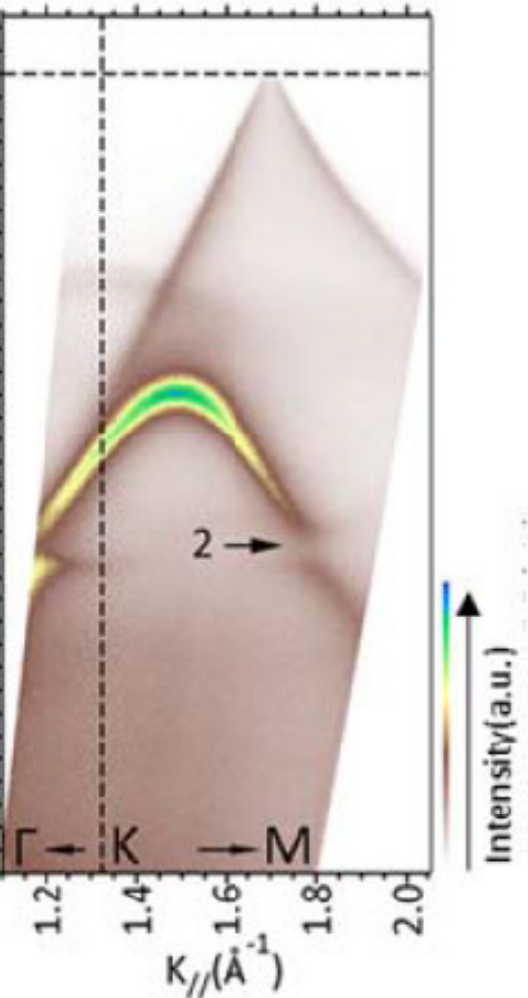
Angle-integrated Intensity



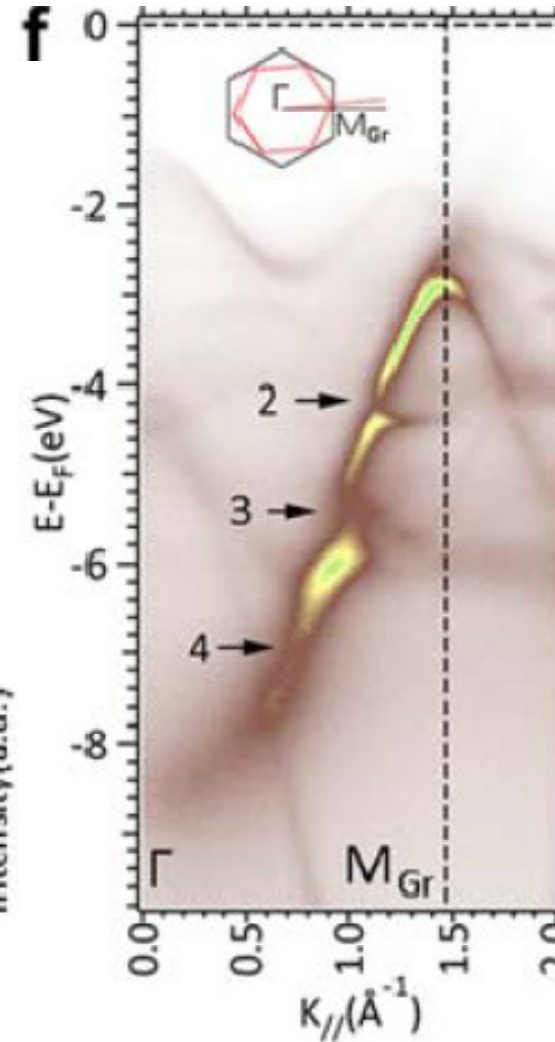
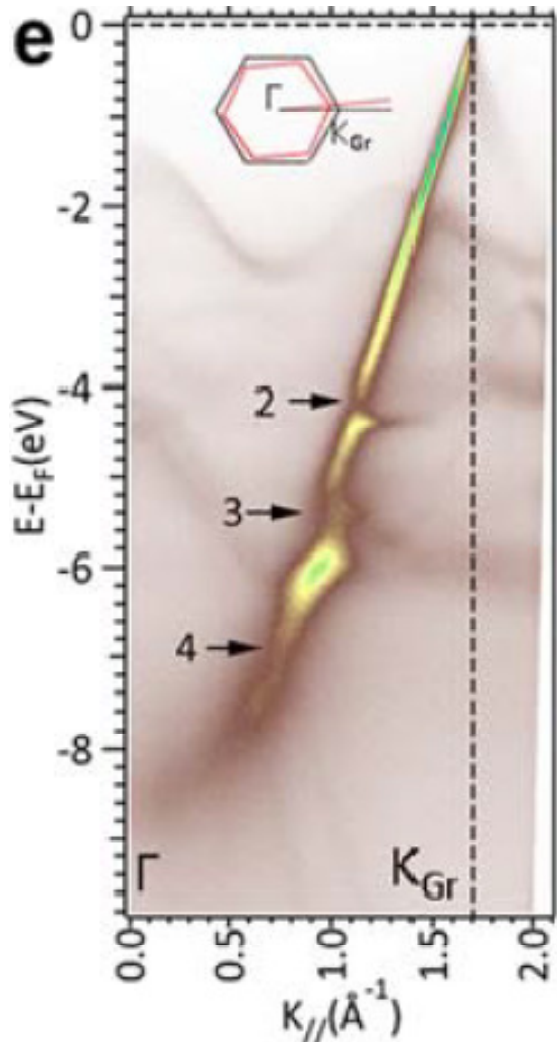
\Rightarrow The Dirac cone of graphene is very close to that expected for free-standing graphene, i.e. linear dispersion and no doping (Fermi-level at the Dirac point).

Band-gaps in graphene π -band

ARPES

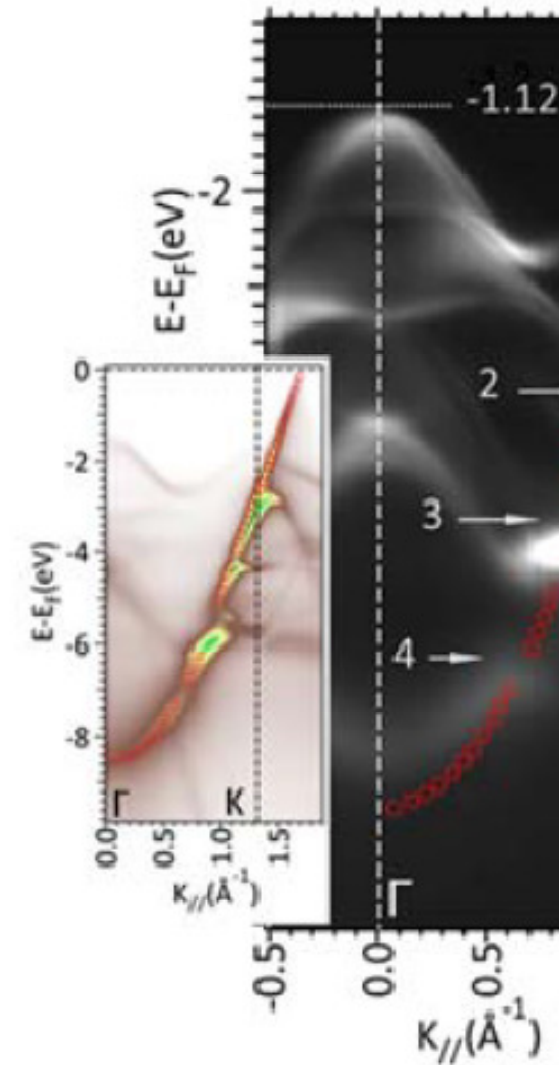
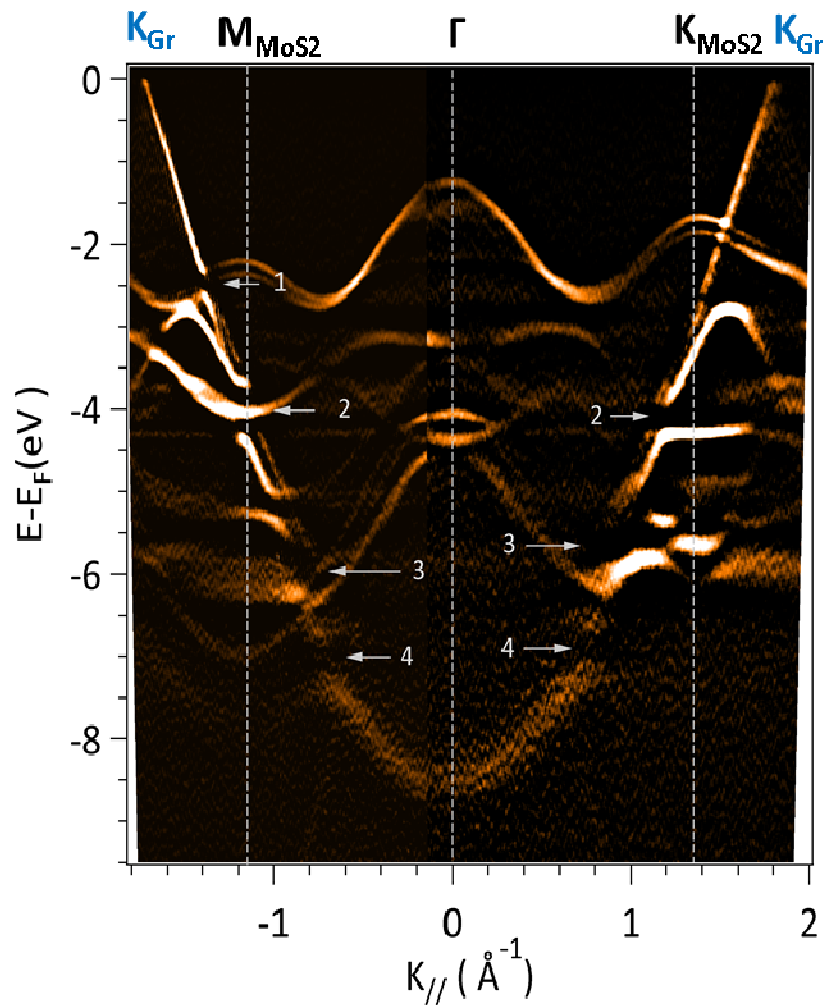


NanoARPES 100 eV



Same gaps in graphene for same substrate-direction => substrate induced

Relation of band-gaps in graphene with MoS₂ 'out-of-plane' orbitals

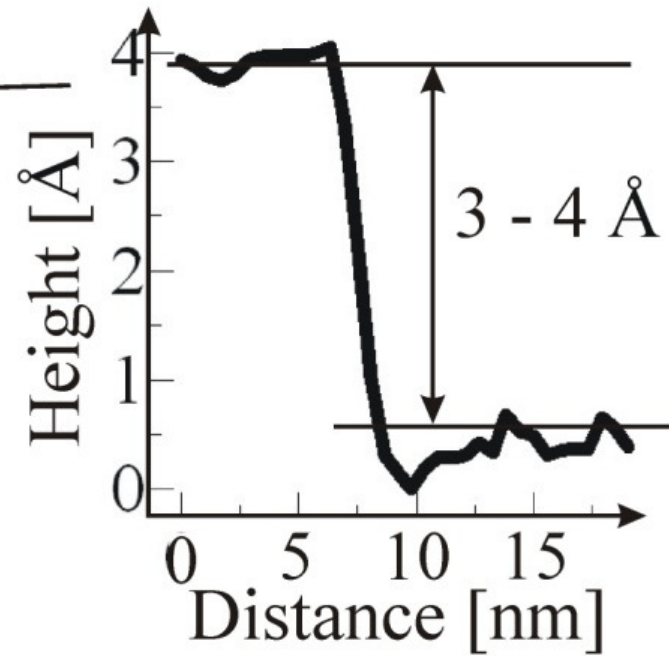
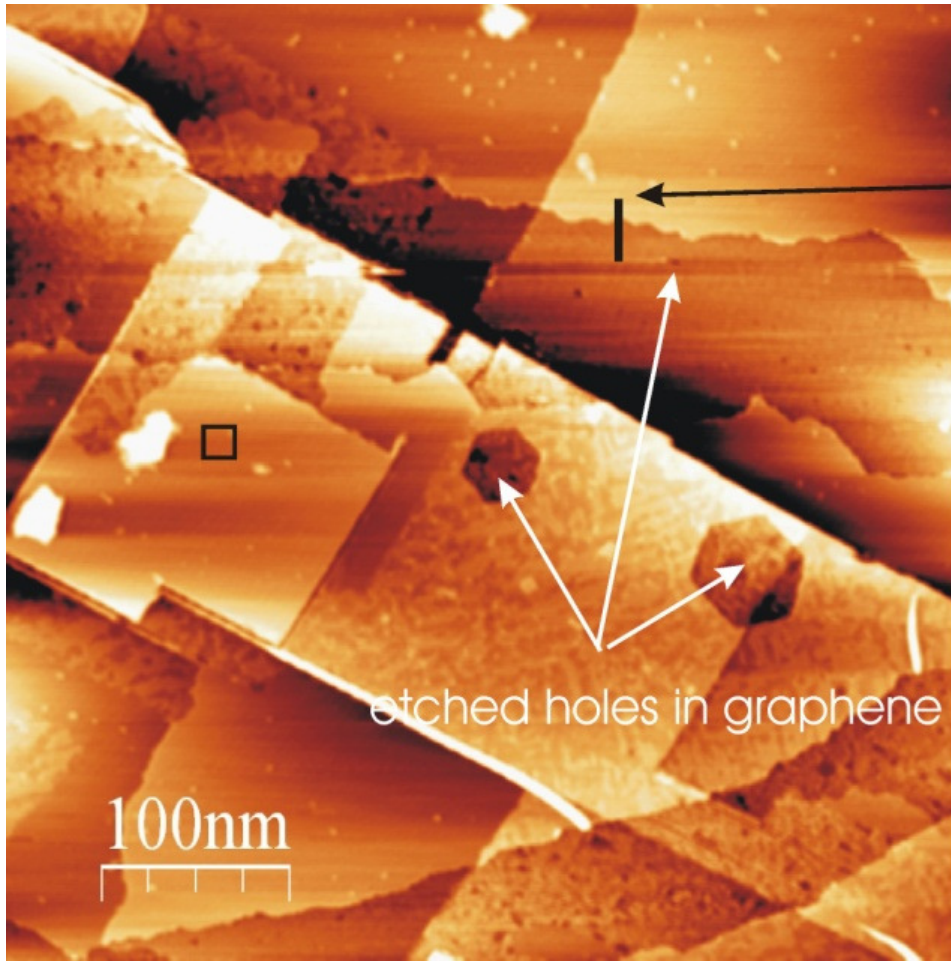


=> Band gaps open in graphene due to hybridization of π -states with 'out-of plane' MoS₂ molecular orbitals

Conclusions: graphene/MoS₂ 'van der Waals' interfaces

- Macroscopic (tens of mm-sized) CVD-grown graphene can be transferred with excellent quality to MoS₂ with atomically sharp and clean interfaces.
- The interface band alignment between graphene and MoS₂ suggests a close to barrier-less electron injection from graphene into MoS₂.
- A close to ideal Dirac-cone of graphene is observed.
- Overlap of out-of-plane molecular orbitals of MoS₂ with graphene π -band causes hybridization and opening of band-gaps in graphene.

Graphene transfer to other materials: e.g. SrTiO₃(001)

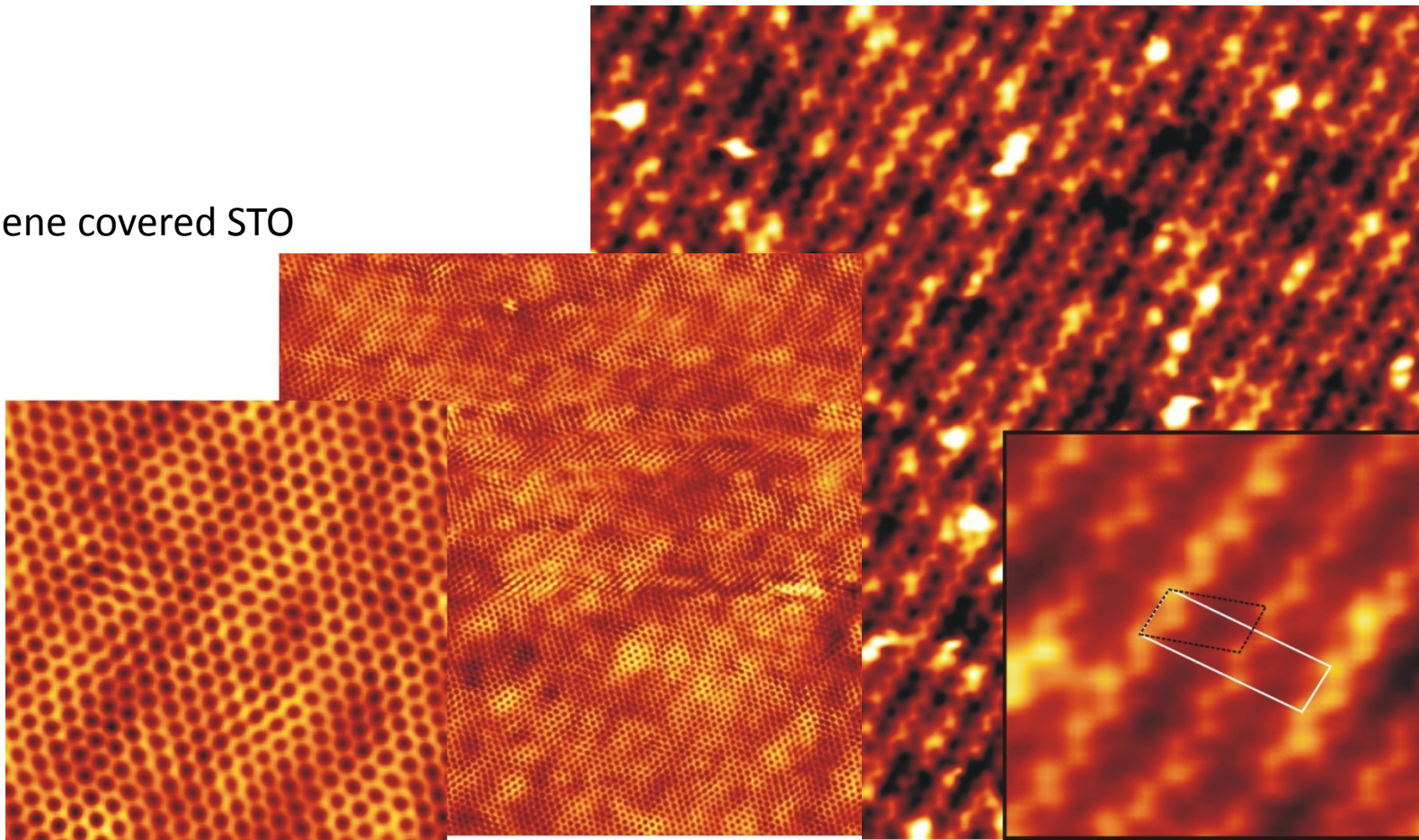


Graphene transfer to other materials: e.g. SrTiO₃(001)

Interface structure of graphene/SrTiO₃(001)

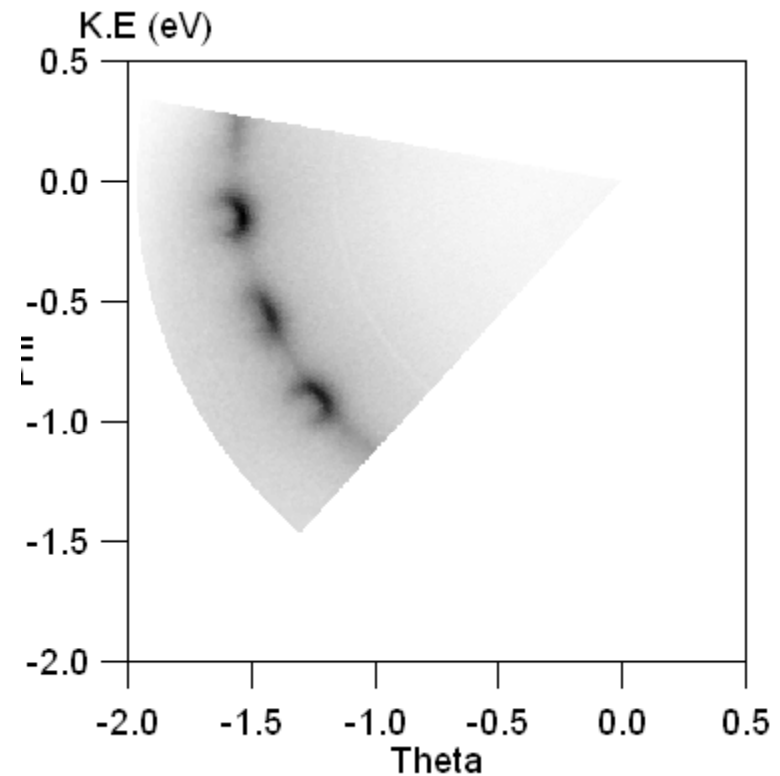
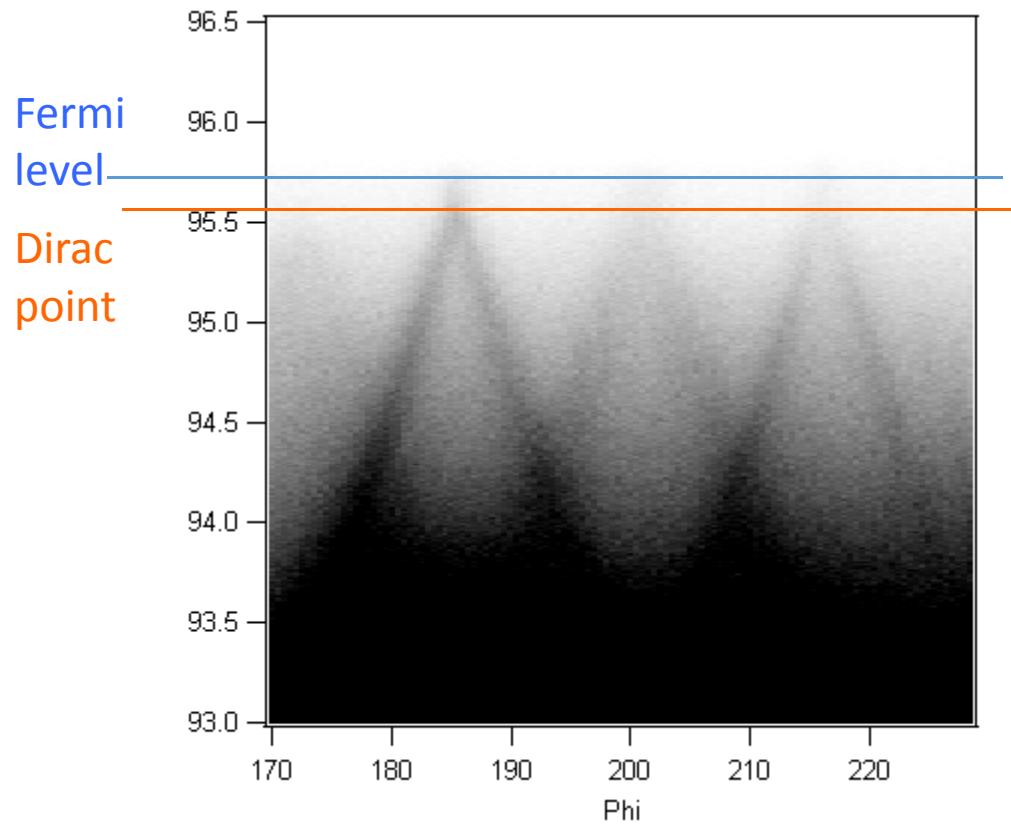
Reconstructed **bare** SrTiO₃ surface.

Graphene covered STO



=>This suggest an atomically sharp interface between graphene and the oxide substrate!

Graphene transfer to other materials: e.g. SrTiO₃(001)



=>Dirac cone of graphene is maintained: Interface charge transfer results in n-type doping

et Us Meet Again

We welcome you all to our future conferences of OMICS Group
International

Please Visit:

<http://materialsscience.conferenceseries.com/>

Contact us at

materialsscience.conference@omicsgroup.us

materialsscience@omicsgroup.com